



STGP7NB60F - STGD7NB60F

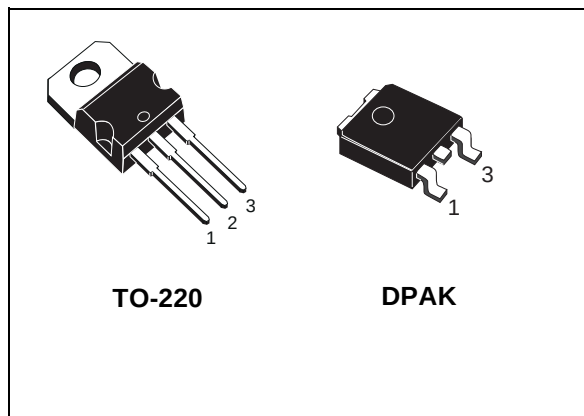
N-CHANNEL 7A - 600V - TO-220 / DPAK

PowerMESH™ IGBT

PRELIMINARY DATA

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _C @100°C
STGP7NB60F	600 V	< 2.4 V	7 A
STGD7NB60F	600 V	< 2.4 V	7 A

- HIGH INPUT IMPEDANCE
- LOW ON-VOLTAGE DROP (V_{cesat})
- OFF LOSSES INCLUDE TAIL CURRENT
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- HIGH FREQUENCY OPERATION
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL (DPAK)



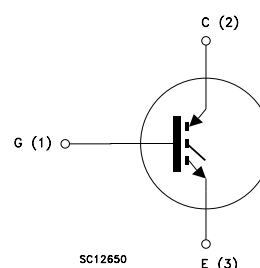
DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "F" identifies a family optimized to achieve very low switching times for frequency applications (<40KHZ)

APPLICATIONS

- MOTOR CONTROLS
- SMPS AND PFC AND BOTH HARD SWITCH AND RESONANT TOPOLOGIES

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		TO-220	DPAK	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600		V
V _{GE}	Gate-Emitter Voltage	±20		V
I _C	Collector Current (continuous) at T _C = 25°C	14		A
I _C	Collector Current (continuous) at T _C = 100°C	7		A
I _{CM} (■)	Collector Current (pulsed)	56		A
P _{TOT}	Total Dissipation at T _C = 25°C	80	70	W
	Derating Factor	0.64	0.56	W/°C
T _{stg}	Storage Temperature	- 55 to 150		°C
T _j	Max. Operating Junction Temperature	150		°C

(■) PULSE WIDTH LIMITED BY SAFE OPERATING AREA

June 2003

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This is preliminary information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

STGP7NB60F - STGD7NB60F**THERMAL DATA**

		TO-220	DPAK	
Rthj-case	Thermal Resistance Junction-case Max	1.56	1.78	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	100	°C/W

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collectro-Emitter Breakdown Voltage	I _C = 250 μA, V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25 °C V _{CE} = Max Rating, T _C = 125 °C			10 100	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ±20V, V _{CE} = 0			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250μA	3		5	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} = 15V, I _C = 7 A V _{GE} = 15V, I _C = 7 A, T _J = 125°C		2 1.5	2.4	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C _{ies}	Input Capacitance	V _{CE} = 25V, f = 1 MHz, V _{GE} = 0			540	pF
C _{oes}	Output Capacitance				80	pF
C _{res}	Reverse Transfer Capacitance				13	pF
Q _g	Total Gate Charge	V _{CE} = 480V, I _C = 7 A, V _{GE} = 15V		37	50	nC
Q _{ge}	Gate-Emitter Charge			4		nC
Q _{gc}	Gate-Collector Charge			18		nC
I _{CL}	Latching Current	V _{clamp} = 480 V T _J = 125°C, R _G = 10 Ω		28		A

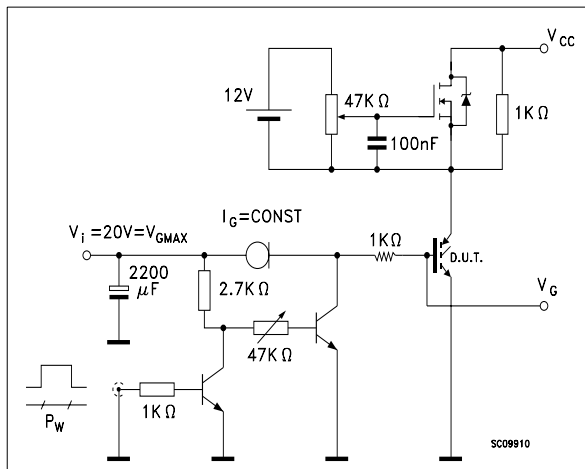
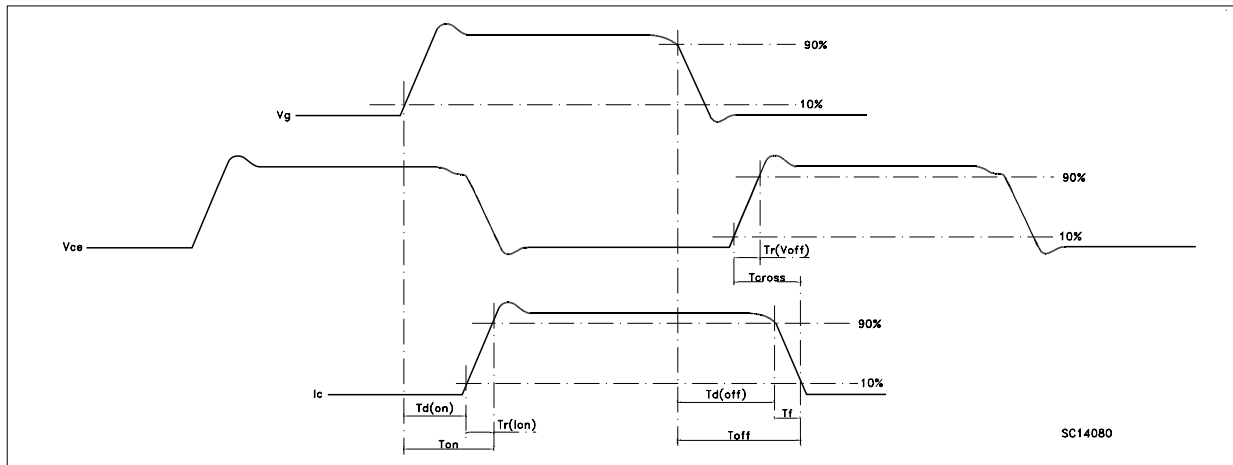
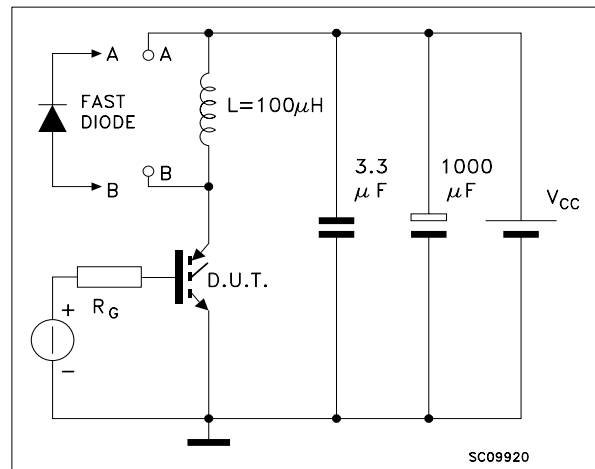
SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on Delay Time	V _{CC} = 480 V, I _C = 7 A R _G = 10Ω, V _{GE} = 15 V		17		ns
t _r	Rise Time			6		ns
(di/dt) _{on}	Turn-on Current Slope	V _{CC} = 480 V, I _C = 7 A R _G =10Ω V _{GE} = 15 V, T _J = 125°C		900		A/μs
E _{on}	Turn-on Switching Losses			60		μJ

STGP7NB60F - STGD7NB60F**ELECTRICAL CHARACTERISTICS (CONTINUED)****SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-over Time	$V_{CC} = 480\text{ V}$, $I_C = 7\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$		190		ns
$t_r(V_{off})$	Off Voltage Rise Time			45		ns
$t_{d(off)}$	Delay Time			110		ns
t_f	Fall Time			140		ns
$E_{off(**)}$	Turn-off Switching Loss			240		μJ
E_{ts}	Total Switching Loss			290		μJ
t_c	Cross-over Time	$V_{CC} = 480\text{ V}$, $I_C = 7\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$		410		ns
$t_r(V_{off})$	Off Voltage Rise Time			135		ns
$t_{d(off)}$	Delay Time			205		ns
t_f	Fall Time			300		ns
$E_{off(**)}$	Turn-off Switching Loss			650		μJ
E_{ts}	Total Switching Loss			625		μJ

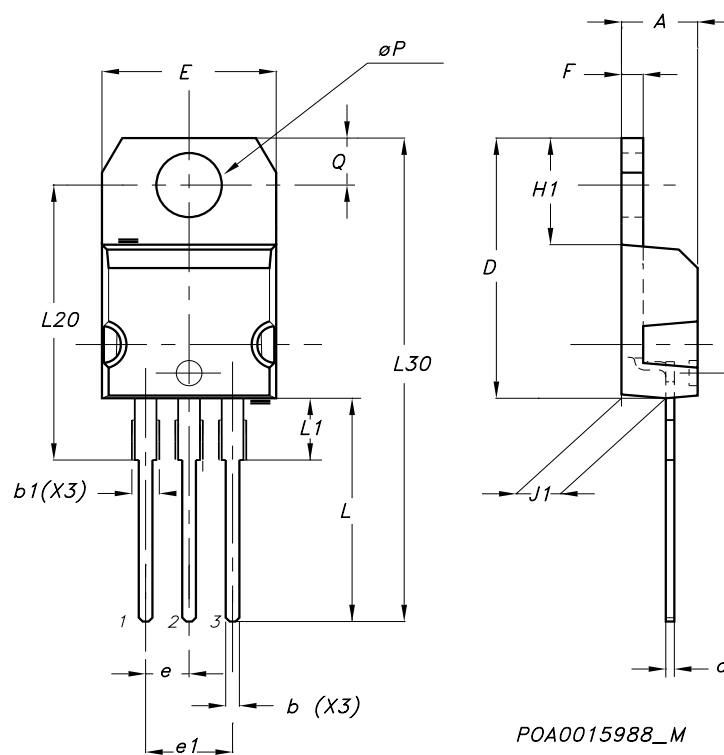
Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
 2. Pulse width limited by max. junction temperature.
 (**) Losses include Also the Tail (Jedec Standardization)

STGP7NB60F - STGD7NB60F**Fig. 1: Gate Charge test Circuit****Fig. 2: Test Circuit For Inductive Load Switching**

STGP7NB60F - STGD7NB60F

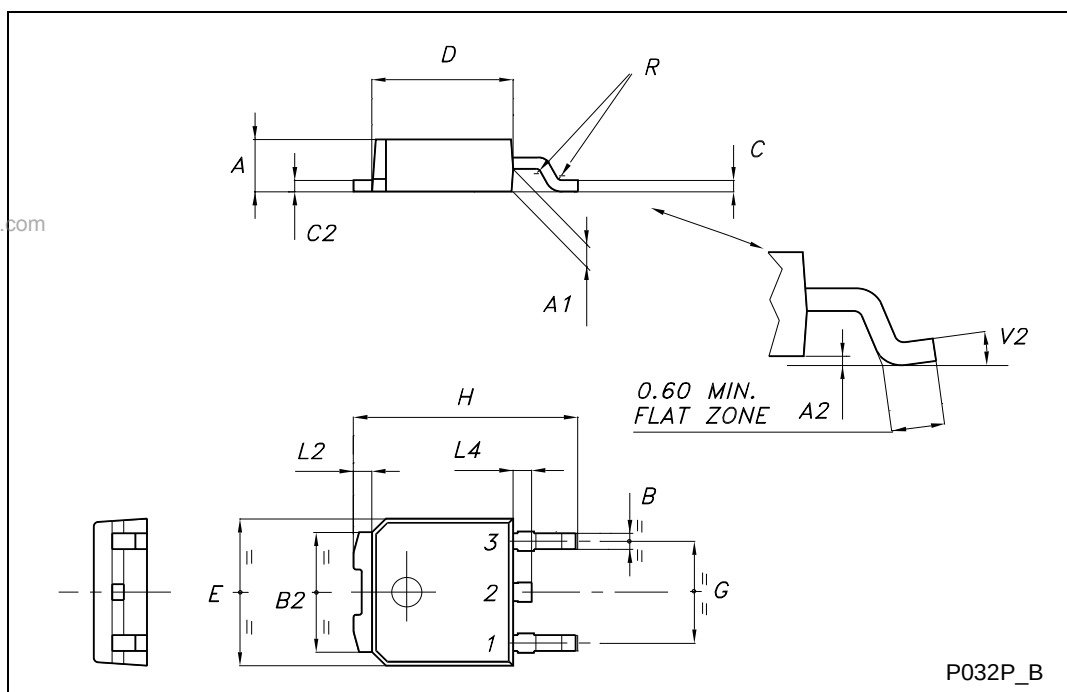
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



STGP7NB60F - STGD7NB60F**TO-252 (DPAK) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



STGP7NB60F - STGD7NB60F

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